

Photon emission by ultra-relativistic positrons in crystalline undulators: the high-energy regime.[★]

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Abstract

This paper discusses the undulator radiation emitted by high-energy positrons during planar channeling in periodically bent crystals. We demonstrate that the construction of the undulator for positrons with energies of 10 GeV and above is only possible if one takes into account the radiative energy losses. The frequency of the undulator radiation depends on the energy of the particle. Thus the decrease of the particle's energy during the passage of the crystal should result in the destruction of the undulator radiation regime. However, we demonstrate that it is possible to avoid the destructive influence of the radiative losses on the frequency of the undulator radiation by the appropriate variation of the shape of the crystal channels. We also discuss a method by which, to our mind, it would be possible to prepare the crystal with the desired properties of its channels.

Key words: undulator radiation, channeling positrons, periodically bent crystal, tapered undulator, strained crystals

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1 Introduction

In this paper we discuss a mechanism, initially proposed in [1,2], for the generation of high-energy photons by means of planar channeling of ultra-relativistic positrons through a periodically bent crystal. In addition to the well-known channeling radiation, there appears an undulator type radiation due to the

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periodic motion of the channeling positrons which follow the bending of the crystallographic planes. The intensity and the characteristic frequencies of this undulator radiation can be easily varied by changing the positrons energy and the parameters of the crystal bending.

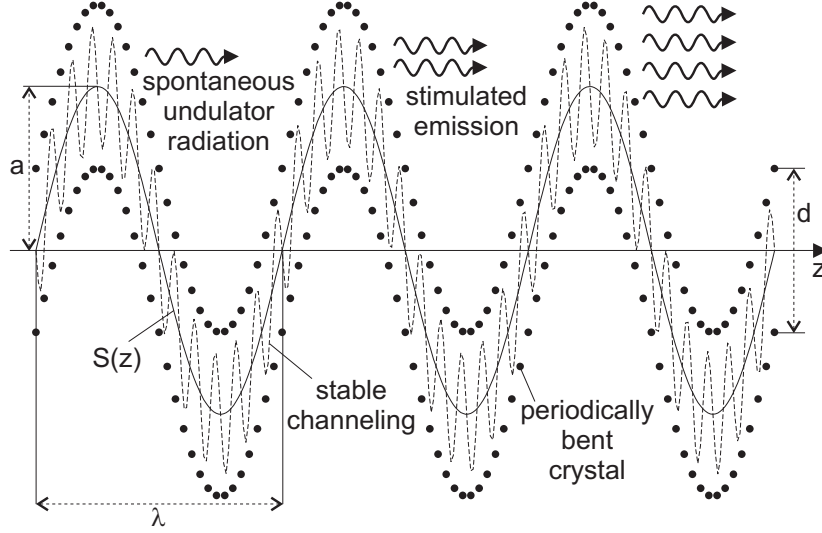


Fig. 1. Schematic figure of the crystalline undulator. The scale in y direction is magnified by a factor $> 10^4$. The function $S(z)$ defines the shape of the centerline of the periodically bent channel.

The mechanism of the photon emission by means of the crystalline undulator is illustrated in figure 1. It is important to stress that we consider the case when the amplitude a of the bending is much larger than the interplanar spacing d ($\sim 10^{-8}$ cm) of the crystal ($a \sim 10 d$), and, simultaneously, is much less than the period λ of the bending ($a \sim 10^{-5} \dots 10^{-4} \lambda$).

In addition to the spontaneous photon emission the scheme leads to the possibility to generate stimulated emission. This is due to the fact, that the photons emitted at the points of maximum curvature of the trajectory travel almost parallel to the beam and thus, stimulate the photon generation in the vicinity of all successive maxima and minima of the trajectory.

We consider two methods for bending the crystal. First, a transverse acoustic wave could be used to bend the crystal dynamically [1,2]. One possibility to create acoustic waves in a crystal is to place a piezo sample atop the crystal and to use radio frequency to excite oscillations. Second, a statically and periodically bent crystal could be constructed using graded strained layers [3]. We will present a detailed description how a static crystalline undulator can be produced.

The conditions for stable channeling has been discussed in [2,4,5]. Channeling only takes place if the maximum centrifugal force in the bent channel, $F_{cf} \approx m\gamma c^2/R_{\min}$ ($R_{\min}$ being the minimum curvature radius of the bent channel),

is less than the maximal force due to the interplanar field, F_{int} which is equal to the maximum gradient of the interplanar field (see [2]). As shown in [4] the ratio $C = F_{\text{cf}}/F_{\text{int}}$ has to be smaller than 0.15, otherwise the phase volume of channeling trajectories is too small. Thus, the inequality $C < 0.15$ connects the energy of the particle, $\varepsilon = m\gamma c^2$, the parameters of the bending (these enter through the quantity R_{min}), and the characteristics of the crystallographic plane.

Another important effect is the dechanneling of the projectiles. The channeling particles scatter with electrons and nuclei of the crystal. These random collisions lead to a gradual increase of the particle energy associated with the transverse oscillations in the channel. As a result, the transverse energy at some distance L_d from the entrance point exceeds the depth of the interplanar potential well, and the particle leaves the channel. The quantity L_d is called the dechanneling length [6] and can be calculated using the methods described in [5,7]. Thus, to consider the undulator radiation formed in a crystalline undulator, it is meaningful to assume that the crystal length does not exceed L_d .

In [5] we estimated the parameters a and λ for given energy ε , regarding the dechanneling length of the bent crystal and the reduction of the phase-space volume due to the bending. For 500 MeV positrons in Si(110) the optimal parameters are $a/d = 10$ and $\lambda = 2.335 \cdot 10^{-3}$ cm. The spectral distribution of the emitted radiation in this case is discussed in the next section (see also [5]).

In the present paper we discuss the possibility to construct undulators to generate photons with energies larger than 1 MeV using positron energies above 10 GeV when the radiative energy losses cannot be neglected and, thus, must be taken into account [4].

The frequency of photons generated in the undulator is determined by the energy of the projectiles and also by the undulator parameter (for definition see equation (1)). In the regime in which the energy of the projectiles is not constant during their passage through the undulator, the frequency of the emitted undulator radiation can nevertheless be kept constant if one chooses the appropriate variation of the shape of the undulator along its length.

We also discuss a method by which, to our mind, it would be possible to prepare crystals with the desired properties of their channels.

2 Spectra of the spontaneous emitted radiation

To illustrate the undulator radiation phenomenon, which we discuss, let us consider the spectra of spontaneous radiation emitted during the passage of positrons through periodically bent crystals.

The photon emission spectra have been calculated using the quasiclassical method [8]. The trajectories of the particles were calculated numerically and then the spectra were evaluated [5]. The latter include both radiation mechanisms, the undulator and the channeling radiation.

Figure 2 shows the spectral distribution of the total radiation emitted in forward direction for $\varepsilon = 500$ MeV positrons channeling in Si along the (110) crystallographic planes. The wavelength of the periodically bent crystal is $\lambda = 2.335 \cdot 10^{-3}$ cm and its amplitude is $a = 10 d$. For the length of the crystal we chose $L_d = 3.5 \cdot 10^{-2}$ cm. This corresponds to $N = 15$ undulator periods.

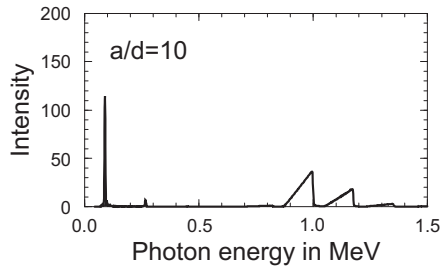


Fig. 2. Spectral distributions of the total radiation emitted in forward direction for $\varepsilon = 500$ MeV positrons channeling in Si along the (110) crystallographic planes for $a/d = 10$.

The first and third harmonic of the undulator radiation are visible on the left side of the spectrum (about 100 keV). The large triangular peak around 1 MeV corresponds to the first harmonic of the channeling radiation. The smaller triangular peaks appear due to the coupling of undulator and channeling radiation. The two types of radiation are well separated and the influence from the channeling radiation on the undulator radiation is negligible small. A detailed discussion of this spectrum is given in [5].

3 Undulator effect in the high-energy regime

The spectra of the emitted radiation presented in the previous section has been calculated in the regime in which the energy losses of the positrons during their passage through the crystal are negligible. In this section, we analyze the opposite situation, which occurs when the energy of the projectiles becomes larger than 10 GeV. On the first glance, the undulator phenomenon can hardly

take place in this energy range, because the energy of positrons during their passage through the crystal can no longer be considered as constant due to the radiative energy losses [4].

Indeed, the frequency $\omega_{\text{und}}^{(1)}$ of the first harmonic of the undulator radiation in the forward direction is given by [2,9]:

$$\omega_{\text{und}}^{(1)} = \frac{4\omega_0\gamma^2}{2 + p_{\text{und}}^2} = \frac{4\pi c\gamma^2(z)}{\lambda + 2\pi^2 \frac{a^2}{\lambda} \gamma^2(z)}. \quad (1)$$

Here we use $\omega_0 = 2\pi c/\lambda$ and the undulator parameter p_{und} is defined as $p_{\text{und}} = \gamma 2\pi a/\lambda$. The shape of the crystal is $S(z) = a \sin(kz)$.

Equation (1) shows that the frequency of the emitted radiation depends on the energy of the projectile. If the decrease of the particle's energy due to the radiative losses is significant ($\gamma(z) < \gamma_0$ for $z > 0$), the frequency $\omega_{\text{und}}^{(1)}$ becomes dependent on the particle's penetration distance z into the crystal. The decrease of the particle's energy leads to the broadening of the undulator lines in the photon emission spectrum and the reduction of their intensity.

However, the monochromaticity of the undulator radiation in the high-energy regime can be restored if one allows the variation of the shape of the crystal channels. Let us consider this condition in more detail and assume that the shape of the channels in the crystal is as follows:

$$S(z) = a(z) \sin(\varphi(z)) \quad (2)$$

with $\varphi(z) = \int_0^z 2\pi/\lambda dz$, $a(z)$ and $\lambda(z)$ are the amplitude and the “period” of the bent crystal channels as function of the penetration depth z .

Let us formulate the conditions for the choice of the shape function $S(z)$. For the given dependence $\gamma(z)$ the functions $a(z)$ and $\lambda(z)$ have to be chosen to keep constant the frequency of the first harmonics, $\omega_{\text{und}}^{(1)}(z) = \text{const.}$ In addition, we require $C(z) = C = \text{const.}$ It was shown in [5,9], that the parameter $C = \varepsilon(z)/(R_{\text{min}}(z) \cdot U'_{\text{max}})$ is characteristic for the channeling process in bent channels and the regime in which the process happens. Here, $R_{\text{min}} \approx \lambda^2(z)/(4\pi a(z))$ is the curvature radius of the shape function $S(z)$ in the points of its extrema.

The two conditions $\omega_{\text{und}}^{(1)}(z) = \text{const.}$ and $C(z) = C = \text{const.}$ and the knowledge of $\gamma(z)$ allow the calculation of $a(z)$ and $\lambda(z)$. Thus the shape $S(z)$ of the crystal is known. For comparatively low energies of the projectile ($\varepsilon < 10$ GeV) the dependence $\gamma(z)$ can be calculated using the approach suggested in [4]. To describe the radiative losses of particles in the high-energy regime,

one has to modify the formulas outlined in [4] and consider the continuously decreasing energy.

Thus, using the initial values ε_0 , a_0 and λ_0 , one can calculate the energy $\varepsilon(z)$ as function of the penetration distance z . Using this dependency we then can calculate the shape $S(z)$ of the channel. The latter, in turn, ensures that the frequency of the undulator radiation and the parameter C remain constant during the passage of the positrons through the crystal, even in the regime in which the radiative energy losses are high. We consider the possibility of the construction of such bent crystals in the next section.

To illustrate the described method we consider positrons with an initial energy of 50 GeV channeling in Si(110). Figure 3 (a) presents the energy of positrons as a function of the penetration depth. We have chosen $C = 0.15$ and the initial amplitude $a_0 = 10d$. These parameters define $\lambda_0 = \sqrt{\varepsilon \pi^2 a d / (U'_{\max} C)} = 2.25 \cdot 10^{-2}$ cm. The argumentation for the choice of C and a one finds in [4] and [5]. The calculated values for $\lambda(z)$ and $a(z)$ are presented in figure 3 (b). Knowing these dependencies, one can easily calculate the shape of the channels.

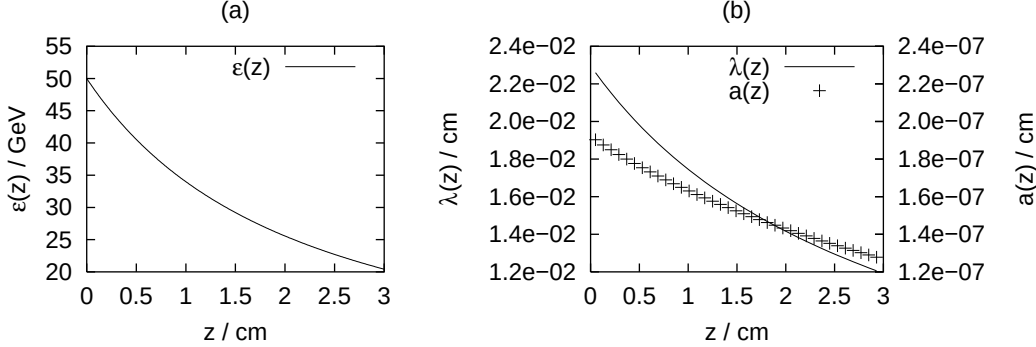


Fig. 3. (a) The energy of the positrons as function of the penetration depth z in the high-energy channeling regime for Si(110) and initial positron energy 50 GeV. The averaging over the possible initial conditions of the positrons was performed as described in [4]. (b) The wavelength λ and the amplitude a of the bent crystal as function of the penetration depth z .

The particle density of channeling positron beams decreases exponentially along the channel [7,9]. The dechanneling length for positrons of $\varepsilon = 50$ GeV and $C = 0.15$ is approximately 1.46 cm and the number of undulator periods on this length is about 75. The emitted undulator radiation should have high intensity and narrow spectral width. The energy of photons at the first harmonic emitted in the forward direction is $\hbar\omega_{\text{und}}^{(1)} = 7.1$ MeV and the spectral width can be estimated as $\Gamma_{\text{und}}^{(1)}/2 = \hbar\omega_{\text{und}}^{(1)}/N_{\text{und}} = 44$ keV.

4 Growing of crystals with periodically bent channels

In this section we propose a method of preparing crystals with periodically bent channels whose shape function $S(z)$ has either the pure sine form, $a \sin kz$, or a more general one defined by (2). In [10] the deflection of proton beams by means of strained crystal layers was demonstrated. The construction of the crystals was described and experimental data that proves the deflection of protons was presented.

Using well-known methods of crystal growing (like molecular beam epitaxy or chemical vapour deposition, see the references in [10]) it is possible to add single crystal layers onto a substrate. Let us consider a pure silicon substrate on which a $\text{Si}_{1-x}\text{Ge}_x$ layer is added (x denotes the germanium content in this layer). The doping with germanium leads to the enlargement of the lattice constant of the added layer. The strain due to the lattice mismatch of the substrate and the $\text{Si}_{1-x}\text{Ge}_x$ layer leads to an increase of the lattice spacing perpendicular to the surface of the substrate (the $\tilde{z}$ -direction in figure 4). The lattice constant parallel to the surface remains unchanged.

Prior to discussing the growing of periodically bent channels, let us summarize the main ideas presented in [10] that we need for our description. The spacing between the (100) layers is $d_{\text{Si}} = 1.358 \text{ \AA}$ in Si and $d_{\text{Ge}} = 1.414 \text{ \AA}$ in Ge. The distance between two $\text{Si}_{1-x}\text{Ge}_x$ layers is given by $d(x) = d_{\text{Si}} + \Delta d \cdot x$, where $\Delta d = d_{\text{Ge}} - d_{\text{Si}}$. In [10] the critical thickness of the strained layer is discussed. If the thickness of the strained layer is larger than the critical value h_c , then lattice defects appear and destruct the channels.

To obtain periodically bent channels, one starts with a pure silicon substrate and adds $\text{Si}_{1-x}\text{Ge}_x$ layers with continuously increasing Ge content. This results in bending of the (110) channels in the direction of the (100) channels. The periodicity of the shape requires the change of the direction of the bending toward the (010) channels. This, in turn, can be achieved by reducing x until it reaches 0. Figure 4 schematically illustrates the first period of the bent (110) channel.

The last crystal layer of the first period consists of pure silicon, so that the second period can be built up on top of the first in the same manner. To be captured by the bent channel, the positron beam should be directed towards the (110) channel of the substrate.

The crystal strain is strongest after half a period, when the germanium content reaches its maximum. The thickness of the layers corresponding to half a period needs to be smaller than the critical thickness h_c . If this condition is met, then crystals with arbitrary number of undulator periods can be constructed.

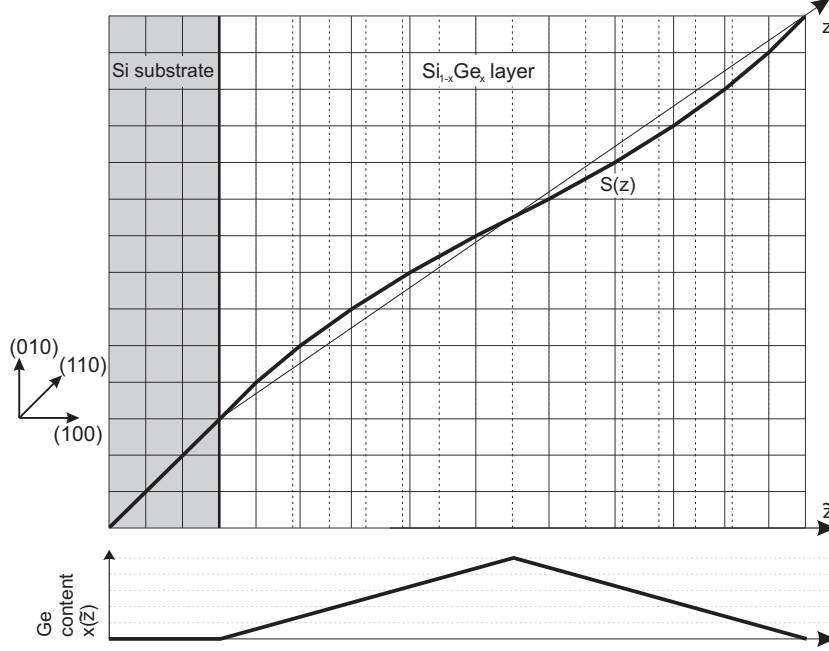


Fig. 4. Schematic figure of the first period of the bent crystal.

For a given shape $S(z)$ it is possible to calculate the germanium content $x(\tilde{z})$ as a function of the thickness $\tilde{z}$ (see figure 4). The formulas can be derived using simple geometric considerations and are discussed in [11]. We now consider two examples.

First we discuss growing the Si crystal with the sine-like shape $S(z) = a \sin kz$ with $a = 10d = 1,92 \cdot 10^{-7}$ cm and $\lambda = 2\pi/k = 2.335 \cdot 10^{-3}$ cm. These parameters correspond to the undulator emission spectrum presented in figure 2 for $a/d = 10$. The germanium content obtained by our calculations is plotted in figure 5.

The maximum germanium content is 5%. The layer thickness that corresponds to half a period is given by $\lambda/(2\sqrt{2}) = 0.8 \cdot 10^{-3}$ cm. The critical thickness h_c for a strained crystal with 5% of Ge is about $1.2 \cdot 10^{-3}$ cm [10].

The second example concerns the shape function given by (2) with $a(z)$ and $\lambda(z)$ as in figure 3 (b). To find the dependence $x(\tilde{z})$ in this case is not so straightforward as for the sine profile. The calculation of $x(\tilde{z})$ results in negative values. To avoid this problem one can consider the crystal growth in the inverse direction: $S(z) \rightarrow S(L_d - z)$ for $0 \leq z \leq L_d$. Then the calculated germanium content is positive for all $\tilde{z} > 0$. The projectiles are injected not through the substrate, as in the first example, but from the opposite side of the crystal. For more details and the analytic description see [11].

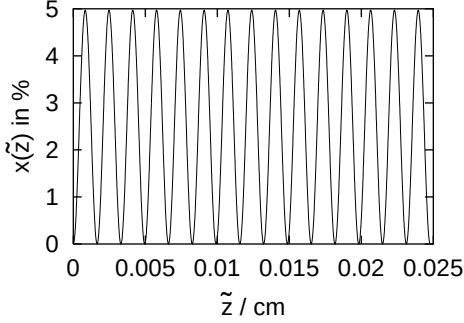


Fig. 5. Germanium content as function of $\tilde{z}$ for a bent Si(110) crystal. The parameters are equal to those used for the calculation of the spectrum shown in figure 2.

5 Summary and outlook

In this work we have discussed the high-energy regime of the undulator radiation emitted by ultra-relativistic positrons channeling in periodically bent crystal channels.

This regime is typical for positron energies well above 10 GeV, when the channeling effect is accompanied by noticeable radiative losses. The latter, being mainly due to the channeling radiation, lead to the gradual decrease of the positron energy. This, in turn, strongly influences the stability of the parameters of the emission of undulator radiation.

We demonstrated that the frequency of the undulator radiation can be maintained constant provided the parameters of the periodic bending are changed with the penetration distance to take into account the decrease of the projectile energy.

Our investigation shows that the discussed modification of the shape of the crystal channels allows the generation of undulator radiation of high-energy photons (up to tens of MeV). The calculation of the spectral distributions of the emitted photons in this regime is currently in progress and will be reported soon.

We described a method that should allow the growing of the crystal channels that are necessary for the experimental measurement of the photon spectra. The feedback from experimentalists would be very helpful to check the predictions, models and assumptions that were used in this work.

Acknowledgements

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